

-20V P-Channel Enhancement Mode MOSFET

General Features

- $V_{DS} = -20V, I_D = -4A$
 $R_{DS(ON)} < 63m\Omega @ V_{GS} = -2.5V$
 $R_{DS(ON)} < 55m\Omega @ V_{GS} = -4.5V$
 ESD Rating: 2500V HBM
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

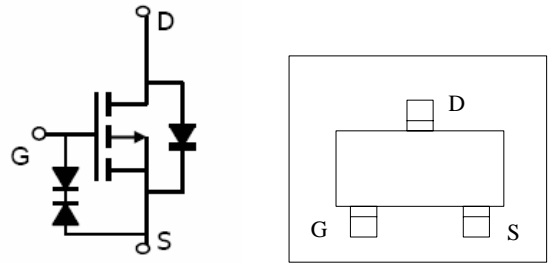
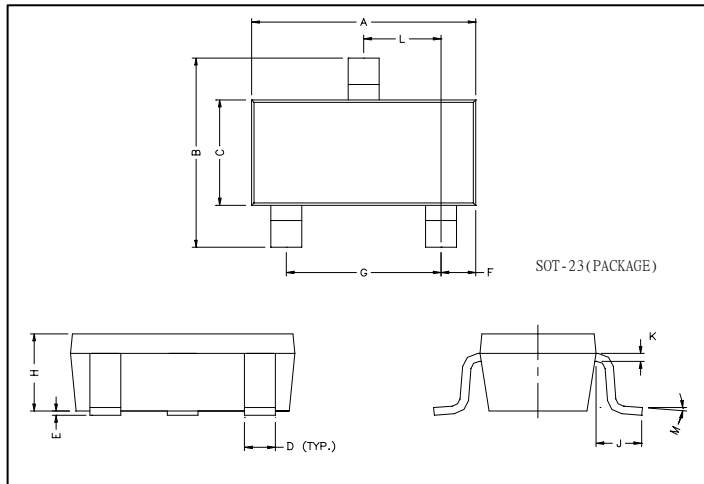
Application

- PWM application
- Load switch

Description

The PT3415 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

Package Dimensions



Schematic diagram

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current-Continuous	I_D	-4	A
Drain Current-Pulsed (Note 1)	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20		-	V

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Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.65	-1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-4A$	-	34.	55	$m\Omega$
		$V_{GS}=-2.5V, I_D=-4A$	-	44	63	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4A$	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	950	-	PF
Output Capacitance	C_{oss}		-	165	-	PF
Reverse Transfer Capacitance	C_{rss}		-	120	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=2.5\Omega$ $V_{GS}=-4.5V, R_{GEN}=3\Omega$	-	12		nS
Turn-on Rise Time	t_r		-	10		nS
Turn-Off Delay Time	$t_{d(off)}$		-	19		nS
Turn-Off Fall Time	t_f		-	25		nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-4A,$ $V_{GS}=-4.5V$	-	12		nC
Gate-Source Charge	Q_{gs}		-	1.4	-	nC
Gate-Drain Charge	Q_{gd}		-	3.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-2.2	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

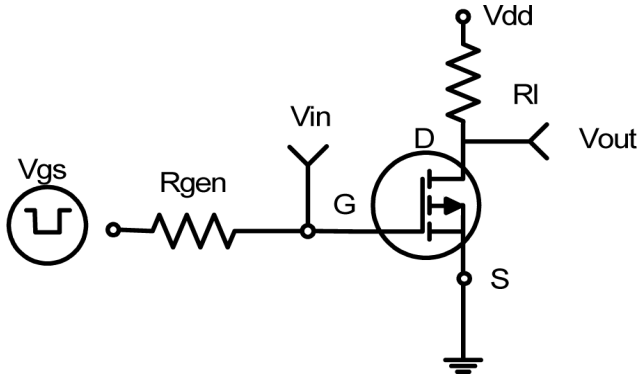


Figure 1: Switching Test Circuit

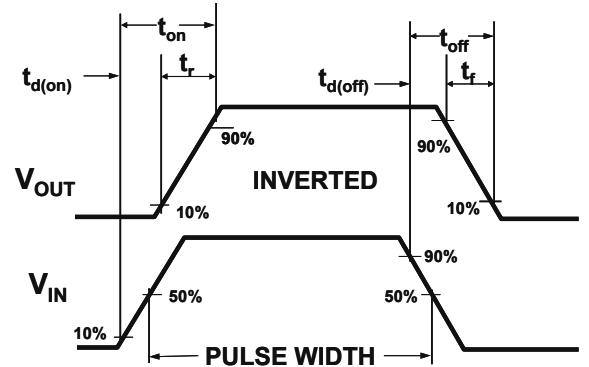


Figure 2: Switching Waveforms

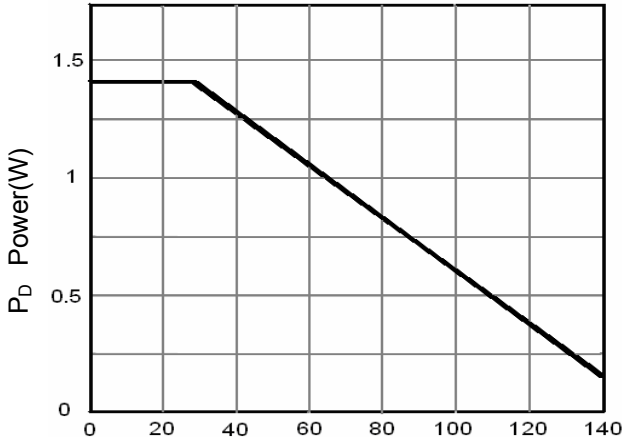


Figure 3 Power Dissipation

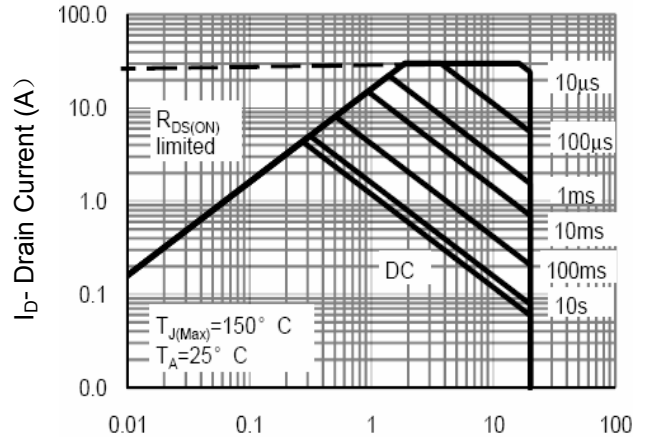


Figure 4 Safe Operation Area

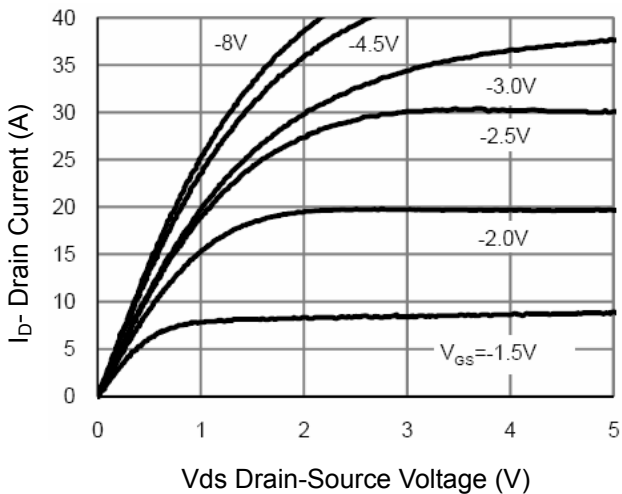


Figure 5 Output CHARACTERISTICS

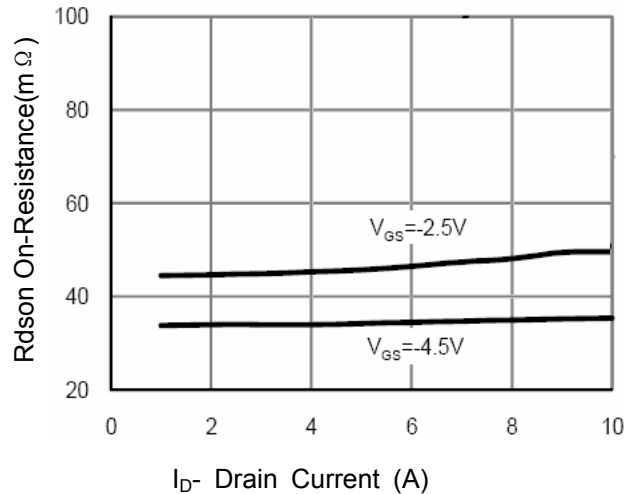


Figure 6 Drain-Source On-Resistance

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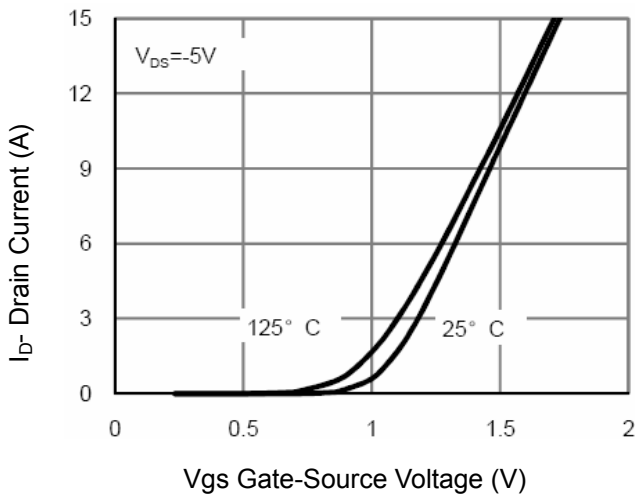


Figure 7 Transfer Characteristics

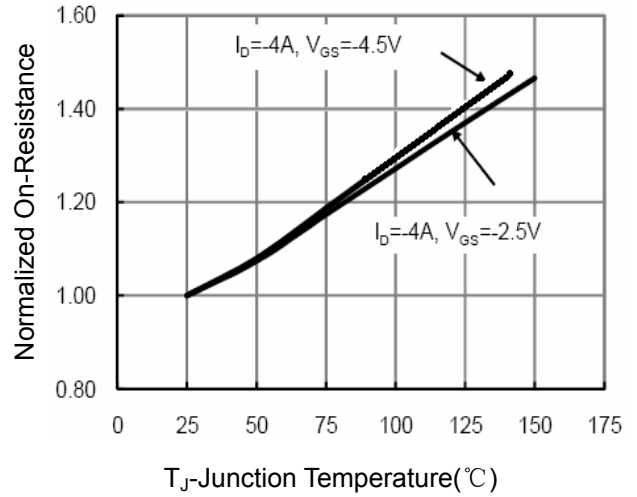


Figure 8 Drain-Source On-Resistance

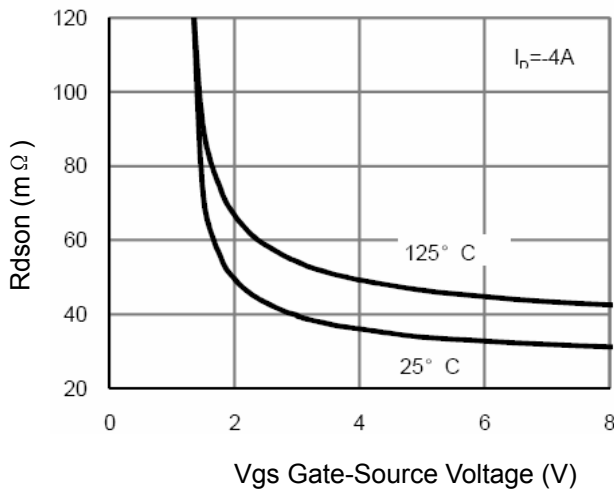


Figure 9 Rdson vs Vgs

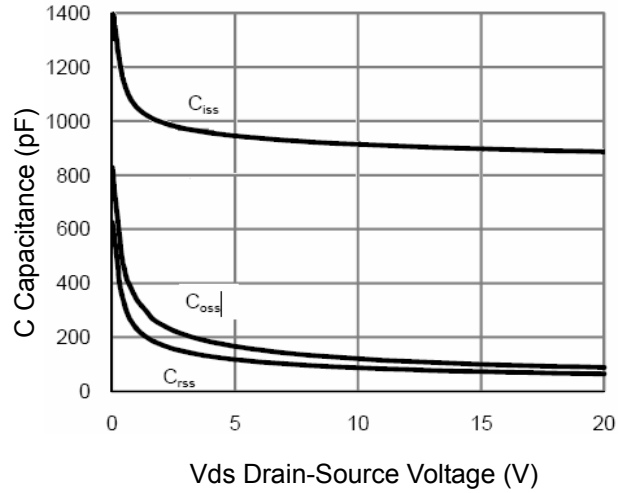


Figure 10 Capacitance vs Vds

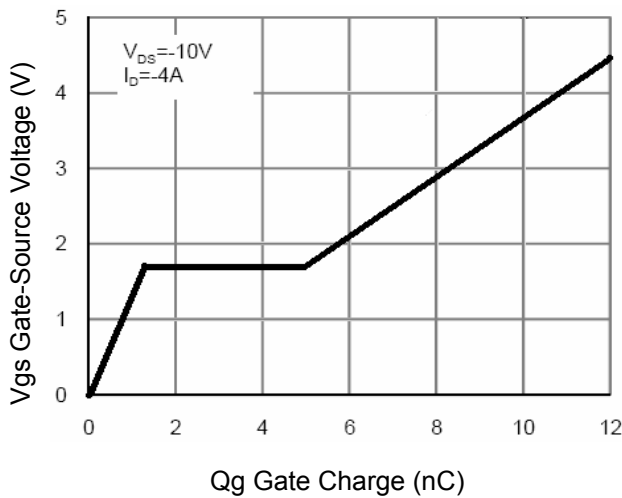


Figure 11 Gate Charge

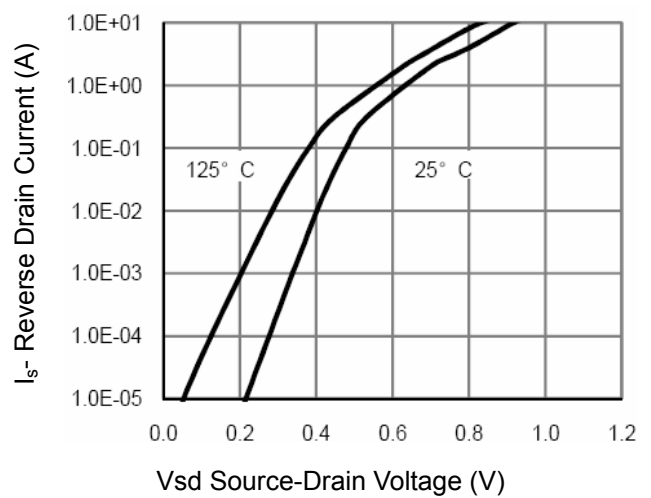


Figure 12 Source- Drain Diode Forward